

REMARKS

Reconsideration and an early allowance are respectfully solicited. Applicants note with appreciation the indication of allowable subject matter.

Claims 1-77 have been cancelled. Claim 78 has been rewritten and is presented in the independent form. Allowed claims 79 and 83 are rewritten and presented in the independent form. Applicants note the withdrawal of claims 86-94 as directed to a non-elected invention.

Applicants respectfully traverse the rejection of Claims 1, 77 and 79 over Masahisa [JP 62-181483]. Masahisa does not disclose or suggest an embodiment in which a metal nitride thin film or the metal oxide thin film is formed on the CaMgS super thin film single crystal 3.

Masahisa discloses that a CaMgS super thin film single crystal 3 is formed on an N-Si single crystal wafer 1, and a ZnS film 2 is formed on the CaMgS super thin film single crystal 3. A CaMgS super thin film single crystal 4 is formed on the ZnS film 2, and an ITO film 5 is formed on the CaMgS super thin film single crystal 4. Above stacked films is covered with Ta₂O₅ element protection film 6.

However, Masahisa does not disclose and suggest "wherein said metal sulfide layer is sandwiched between said single crystal silicon substrate and said thin film, comprising an ionic compound, and wherein said thin film comprising said ionic compound is selected from the group consisting of a metal nitride thin film and a metal oxide thin film" as for example in claim 78 of the present application. In Masahisa, a metal sulfide layer formed on a single crystal silicon substrate (N-Si single crystal wafer 1) is the CaMgS super thin film single crystal 3, and the ZnS film 2 (metal sulfide thin film) as a thin film comprising an ionic compound is formed on the CaMgS super thin film single crystal 3. That is, in Masahisa, components sandwiching the metal sulfide

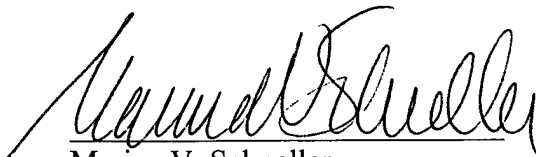
layer are the N-Si single crystal wafer 1 and the thin film comprising an ionic compound which is the metal sulfide thin film. In contrast, ionic compound which is the metal sulfide thin film. In contrast, in Claim 78, the components sandwiching the metal sulfide layer are the single crystal silicon substrate and a thin film comprising an ionic compound which is a metal nitride thin film or a metal oxide thin film.

Masahasi discloses a ZnS film 2 which is the metal sulfide thin film is formed on the CaMgS super thin film single crystal 3; in summary, Masahisa does not disclose and suggest that the metal nitride thin film or the metal oxide thin film is formed on the CaMgS super thin film single crystal 3.

Reconsideration and an early allowance are respectfully solicited.

Respectfully submitted,

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